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4/28/03
AMENDMENT UNDER 37 C.F.R. § 1.116
EXPEDITED PROCEDURE
GROUP 2815
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q61741

Takashi UDAGAWA ✓

Appln. No.: 09/881,782 ✓

Group Art Unit: 2815

Confirmation No.: 1610

Examiner: Paul E. Brock II

Filed: June 18, 2001 ✓

For: GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, LIGHT
EMITTING DIODE LAMP, LIGHT SOURCE, ELECTRODE FOR GROUP-III NITRIDE
SEMICONDUCTOR LIGHT-EMITTING DIODE, AND METHOD FOR PRODUCING
THE ELECTRODE ✓

AMENDMENT UNDER 37 C.F.R. § 1.116

FAX RECEIVED

ATTN: BOX AF

APR 18 2003

Commissioner for Patents
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

Sir:

This Amendment is submitted in response to the Office Action dated December 18, 2002.

Please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 21 without prejudice or disclaimer.

Please enter the following amended claims:

Sub E1
D1
1. (Three Times Amended) A group-III nitride semiconductor light-emitting diode
comprising at least a first conduction-type single crystal substrate provided with a first
conduction-type back-surface ohmic electrode on a back surface thereof, a buffer layer